

NSS1C201MZ4T3G Datasheet

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DiGi Electronics Part Number NSS1C201MZ4T3G-DG

Manufacturer onsemi

Manufacturer Product Number NSS1C201MZ4T3G

Description TRANS NPN 100V 2A SOT223

Detailed Description Bipolar (BJT) Transistor NPN 100 V 2 A 100MHz 800

mW Surface Mount SOT-223 (TO-261)



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
NSS1C201MZ4T3G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	2 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
100 V	180mV @ 200mA, 2A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	120 @ 500mA, 2V
Power - Max:	Frequency - Transition:
800 mW	100MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-261-4, TO-261AA	SOT-223 (TO-261)
Base Product Number:	
NSS1C201	

Environmental & Export classification

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



100 V, 2.0 A, Low V_{CE(sat)} **NPN Transistor NSS1C201MZ4. NSV1C201MZ4**

onsemi's e²PowerEdge family of low V_{CE(sat)} transistors are miniature surface mount devices featuring ultra low saturation voltage (V_{CE(sat)}) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	100	Vdc
Collector-Base Voltage	V _{CBO}	140	Vdc
Emitter-Base Voltage	V _{EBO}	7.0	Vdc
Collector Current - Continuous	I _C	2.0	Α
Collector Current - Peak	I _{CM}	3.0	Α

THERMAL CHARACTERISTICS

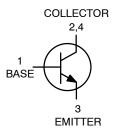
Characteristic	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 1)	800 6.5	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	155	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 2)	2.0 15.6	W mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	64	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P _{Dsingle} (Note 3)	710	mW
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

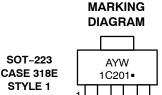
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

- 1. FR-4 @ 7.6 mm², 1 oz. copper traces. 2. FR-4 @ 645 mm², 1 oz. copper traces.
- 3. Thermal response.

100 VOLTS, 2.0 AMPS NPN LOW $V_{CE(sat)}$ TRANSISTOR



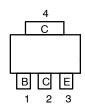


= Assembly Location

= Year W = Work Week

1C201 = Specific Device Code = Pb-Free Package

PIN ASSIGNMENT



Top View Pinout

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS1C201MZ4T1G NSV1C201MZ4T1G	SOT-223 (Pb-Free)	1000/ Tape & Reel
NSS1C201MZ4T3G	SOT-223 (Pb-Free)	4000/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSS1C201MZ4, NSV1C201MZ4

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	100			Vdc
Collector – Base Breakdown Voltage (I _C = 0.1 mAdc, I _E = 0)	V _{(BR)CBO}	140			Vdc
Emitter – Base Breakdown Voltage ($I_E = 0.1 \text{ mAdc}, I_C = 0$)	V _{(BR)EBO}	7.0			Vdc
Collector Cutoff Current (V _{CB} = 140 Vdc, I _E = 0)	I _{CBO}			100	nA
Emitter Cutoff Current (V _{EB} = 6.0 Vdc)	I _{EBO}			50	nA
ON CHARACTERISTICS					
DC Current Gain (Note 4) ($I_C = 10 \text{ mA}$, $V_{CE} = 2.0 \text{ V}$) ($I_C = 500 \text{ mA}$, $V_{CE} = 2.0 \text{ V}$) ($I_C = 1.0 \text{ A}$, $V_{CE} = 2.0 \text{ V}$) ($I_C = 2.0 \text{ A}$, $V_{CE} = 2.0 \text{ V}$)	h _{FE}	150 120 80 40		360	
Collector – Emitter Saturation Voltage (Note 4) ($I_C = 0.1 \text{ A}$, $I_B = 0.010 \text{ A}$) ($I_C = 0.5 \text{ A}$, $I_B = 0.050 \text{ A}$) ($I_C = 1.0 \text{ A}$, $I_B = 0.100 \text{ A}$) ($I_C = 2.0 \text{ A}$, $I_B = 0.200 \text{ A}$)	V _{CE} (sat)			0.030 0.060 0.100 0.180	V
Base – Emitter Saturation Voltage (Note 4) $(I_C = 1.0 \text{ A}, I_B = 0.100 \text{ A})$	V _{BE(sat)}			1.10	V
Base – Emitter Turn–on Voltage (Note 4) (I _C = 1.0 A, V _{CE} = 2.0 V)	V _{BE(on)}			0.850	V
Cutoff Frequency (I _C = 100 mA, V _{CE} = 5.0 V, f = 100 MHz)	f _T		100		MHz
Input Capacitance (V _{EB} = 0.5 V, f = 1.0 MHz)	Cibo		305		pF
Output Capacitance (V _{CB} = 3.0 V, f = 1.0 MHz)	Cobo		22		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

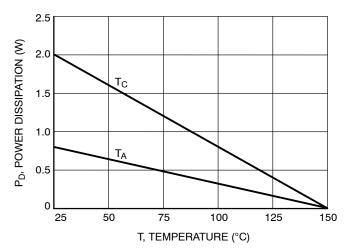


Figure 1. Power Derating

NSS1C201MZ4, NSV1C201MZ4

TYPICAL CHARACTERISTICS

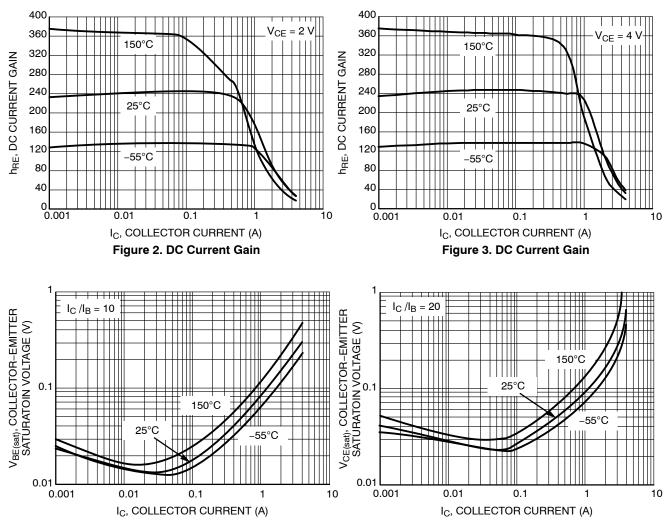


Figure 4. Collector-Emitter Saturation Voltage

Figure 5. Collector-Emitter Saturation Voltage

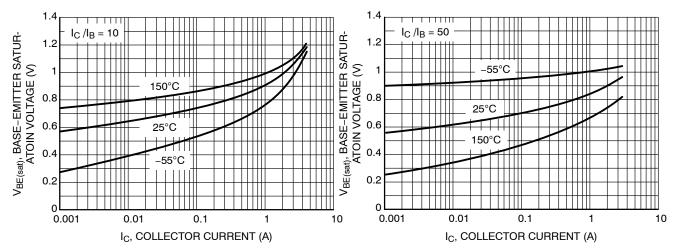
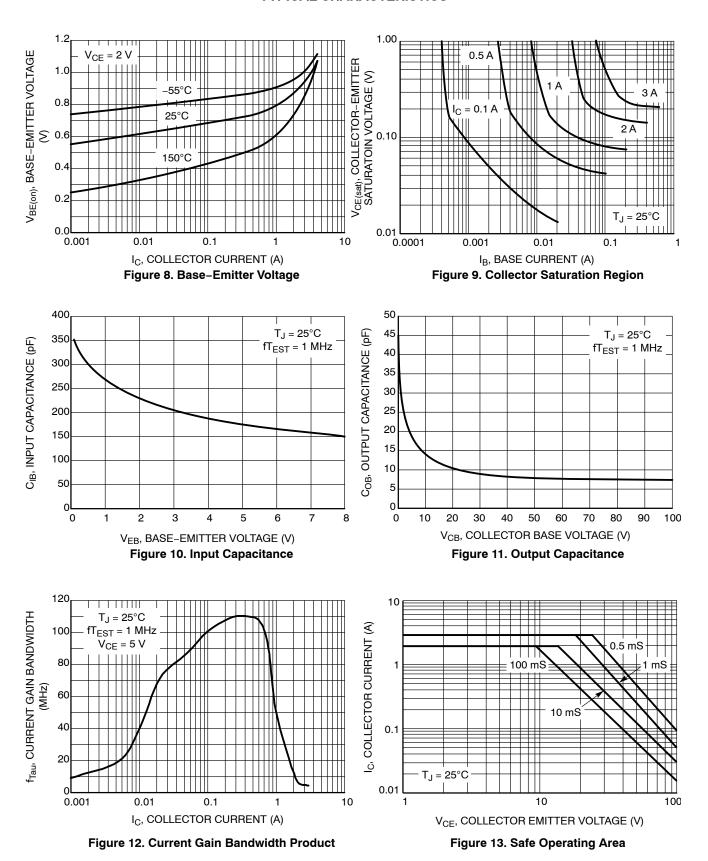


Figure 6. Base-Emitter Saturation Voltage

Figure 7. Base-Emitter Saturation Voltage

NSS1C201MZ4, NSV1C201MZ4

TYPICAL CHARACTERISTICS



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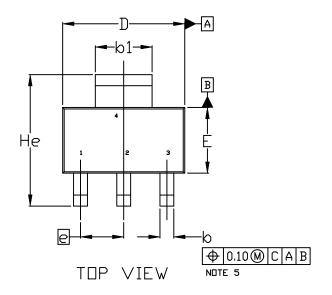


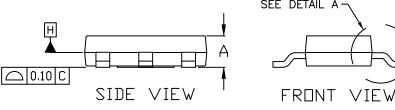
MECHANICAL CASE OUTLINE

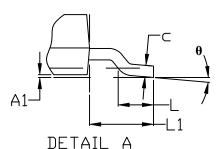
PACKAGE DIMENSIONS

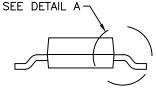


DATE 02 OCT 2018





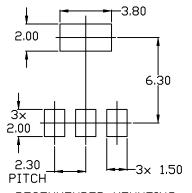




NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
b	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
c	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
е		2.30 BSC	;	
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0*		10°	



RECOMMENDED MOUNTING **FOOTPRINT**

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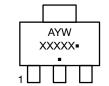
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DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*



A = Assembly Location

Y = Year

W = Work Week
XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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